

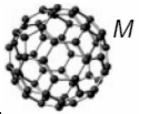
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M.N.Kiselev

Kondo Shuttling





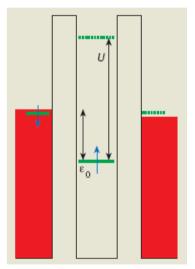
Workshop on Quantum Pumping, Haifa, January 8, 2007

Single orbital level coupled to two leads



$$H = H_{leads} + H_{tun} + H_{dot}$$

$$H_{leads} = \sum_{k,\sigma\alpha=L,R} [\epsilon_k - \mu_\alpha] c^{\dagger}_{k,\sigma\alpha} c_{k,\sigma\alpha}$$



$$H_{tun} = \sum_{k,\sigma\alpha} [V_{\alpha}(t)c_{k,\sigma\alpha}^{\dagger}d_{\sigma} + H.c.]$$

$$H_{dot} = \sum_{\sigma} \varepsilon_0 d_{\sigma}^{\dagger} d_{\sigma} + U(n-N)^2$$

Tunneling width

$$\Gamma_{\alpha}(t) = \pi \rho |V_{\alpha}|^2(t)$$

Single orbital level coupled to two leads

Time-dependent Glazman-Raikh rotation

$$\begin{pmatrix} c_{k\sigma L} \\ c_{k\sigma R} \end{pmatrix} = U_t \begin{pmatrix} c_{k\sigma +} \\ c_{k\sigma -} \end{pmatrix} \qquad U_t = \begin{pmatrix} \cos \theta_t & -\sin \theta_t \\ \sin \theta_t & \cos \theta_t \end{pmatrix}$$
$$\tan \theta_t = \left| \frac{V_R(t)}{V_L(t)} \right| \qquad |V|^2(t) = |V_L|^2(t) + |V_R|^2(t)$$
$$H_{Berry} = \sum_{k,\sigma\gamma=\pm} \left(c_{k,\sigma+}^{\dagger} c_{k,\sigma-}^{\dagger} \right) \left[-iU_t^{-1} \frac{\partial U_t}{\partial t} \right] \begin{pmatrix} c_{k,\sigma+} \\ c_{k,\sigma-} \end{pmatrix}$$
$$a_t = \frac{d\theta_t}{dt} \begin{pmatrix} 0 & i \\ -i & 0 \end{pmatrix}$$
Tomosuke Aono, 200

Adiabatic current and pumped charge per cycle at T=0

$$I_{\sigma} = \frac{e}{2\pi} \left[-\frac{d\theta_{t}}{dt} \sin(2\theta_{t}) \sin(2\delta_{\sigma}(t)) + \frac{d\delta_{\sigma}}{dt} \cos(2\theta_{t}) \right]$$
Scattering phase shifts at the Fermi level in the leads

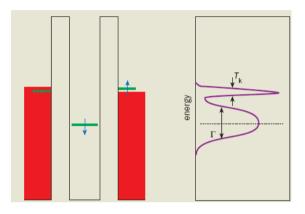
$$Q_{\sigma} = \oint dt I_{\sigma}(t) = \frac{e}{2\pi} \oint dt (1 - T_{\sigma}) \frac{d\Upsilon_{\sigma}}{dt}$$

$$T_{\sigma} = \sin^{2}(2\theta_{t}) \sin^{2} \delta_{\sigma}(t)$$

$$\Upsilon_{\sigma} = \arctan[\cos^{2}(2\theta_{t}) \tan \delta_{\sigma}(t)]$$

$$Q_{\sigma} = \frac{e}{2\pi} \oint (\cos(2\theta) d\delta_{\sigma} - \sin(2\theta) \sin(2\delta_{\sigma}) d\theta)$$
Adiabaticity $\hbar\Omega \ll \min[\Gamma(t)]$ M.Büttiker et al, 1994

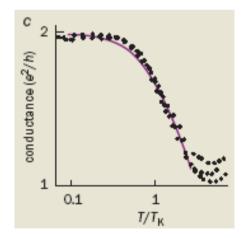
Adiabatic pumping at the Kondo regime



$$\delta_{\sigma}
ightarrow rac{\pi}{2}$$

Nozieres Fermi Liquid regime

$$T_K = \sqrt{(\Gamma_L + \Gamma_R)U/\pi} \exp\left[-\frac{\pi U}{4(\Gamma_L + \Gamma_R)}\right]$$



Pumped charge $Q_c = Q_\uparrow + Q_\downarrow = 0$ Pumped spin

$$Q_s = Q_{\uparrow} - Q_{\downarrow} \neq 0$$

Kondo Pump = Resonance Spin Diode

What if $\Gamma(t)$ is due to a nanomechanics?

Molecular Transistor

Nano-Pendulum

205nm

Au

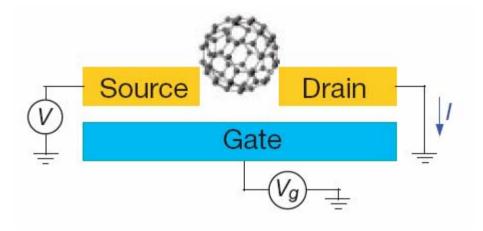
Si

bias-tee

Vac

v

GND =



H.Park et al, Nature 2000

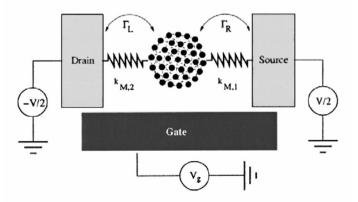
D.Sheible and R.Blick 2004

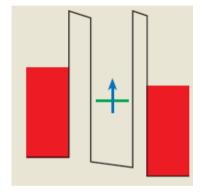
 $p < 10^{-3}$ mbar

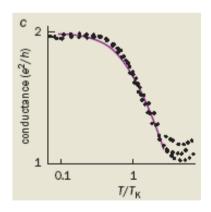
NanoElectroMechanical Pump = Shuttle

Why do we look for the Kondo effect in nano-devices ?

- The Kondo effect makes it easier for states belonging to the two opposite electrodes to mix
- Reasonably high Kondo temperatures > 1 K
- SETs are highly controllable (by bias, magnetic field etc) devices







Keeping in mind Pumping ... I will speak about Shuttling.

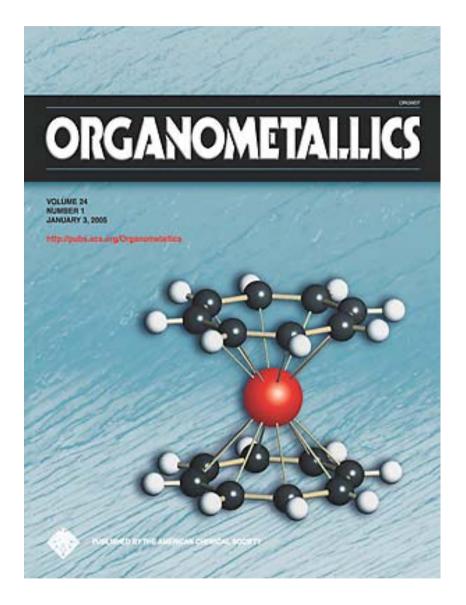
How to make the Kondo effect work in the Nanoelectromechanical devices?

How is the KE influenced by the NEM?

 \cdot the nano-device changes its shape in the process of the tunneling

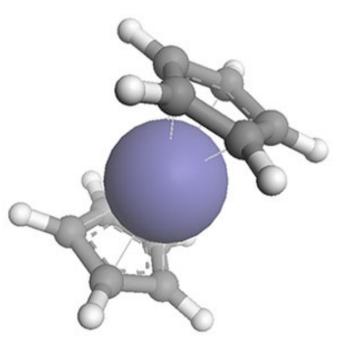
• the nano-devise is nano-machined by external periodic force

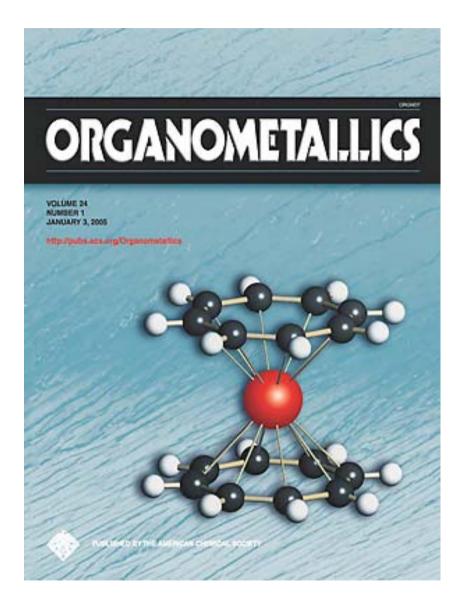
K.Kikoin, MK and M.R.Wegewijs, PRL 2006 MK, K.Kikoin, R.Shekhter and V.Vinokur, PRB 2006



Ferrocene

$Fe(C_5H_5)_2$

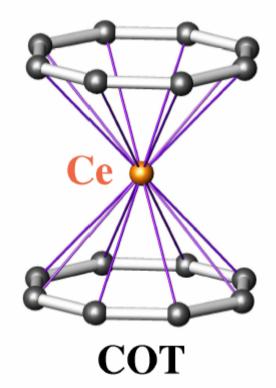




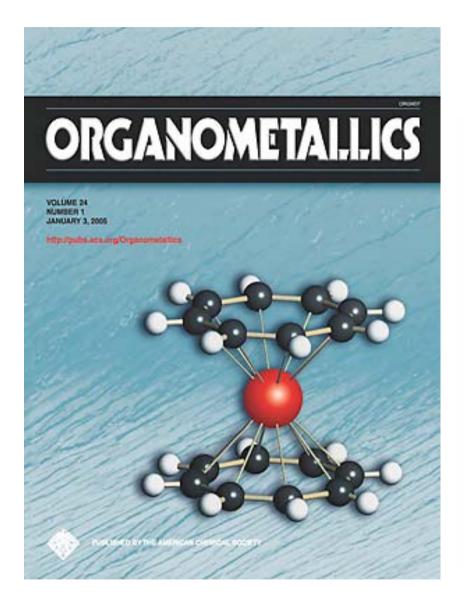
Cerocene

 $Ce(C_8H_8)_2$

Ce(COT)₂

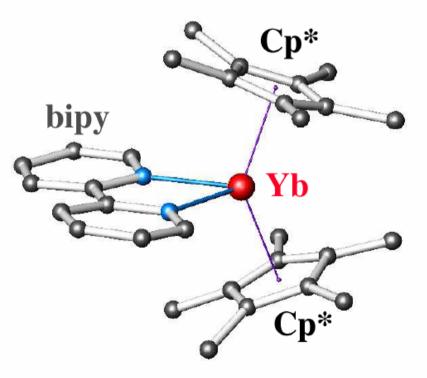


COT = C8H8

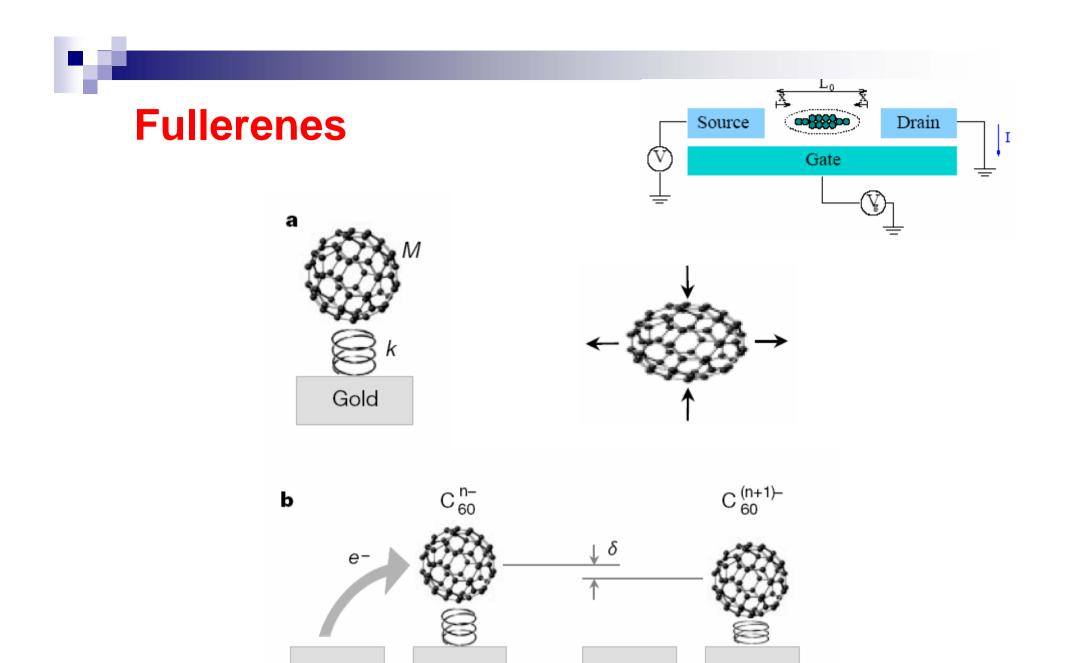


Ytterbocene

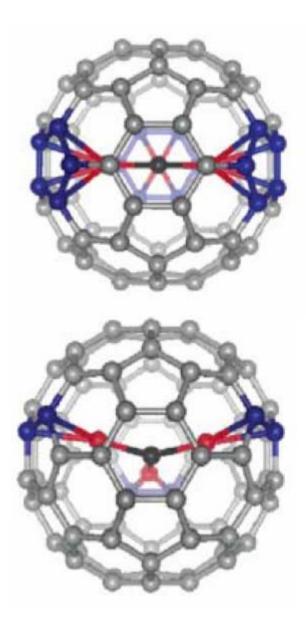
Cp*₂Yb(bipy)

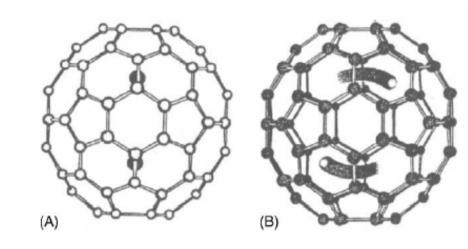


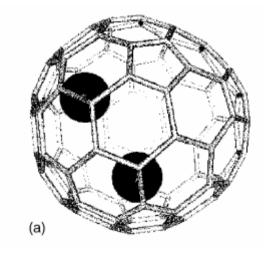
 $Cp^* = C5Me5$, bipy = (NC5H4)2]



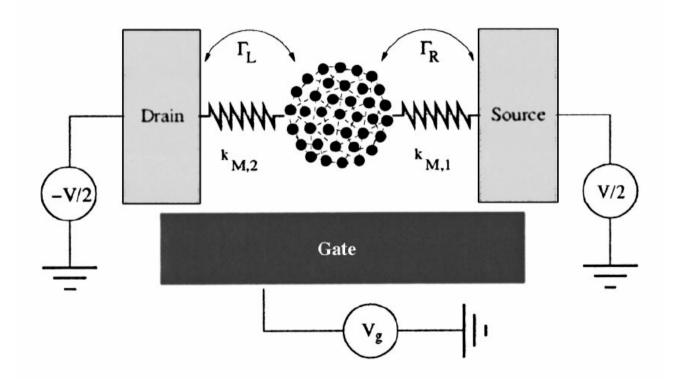
Transition metals inside fullerens







Transport through molecular transistors



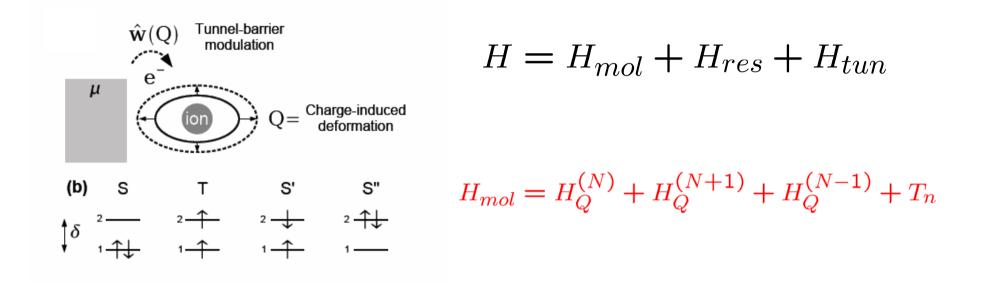
Q: Whether phonons support or destroy Kondo effect?

A: Usually they destroy it due to the energy transfer and the decoherence effects.

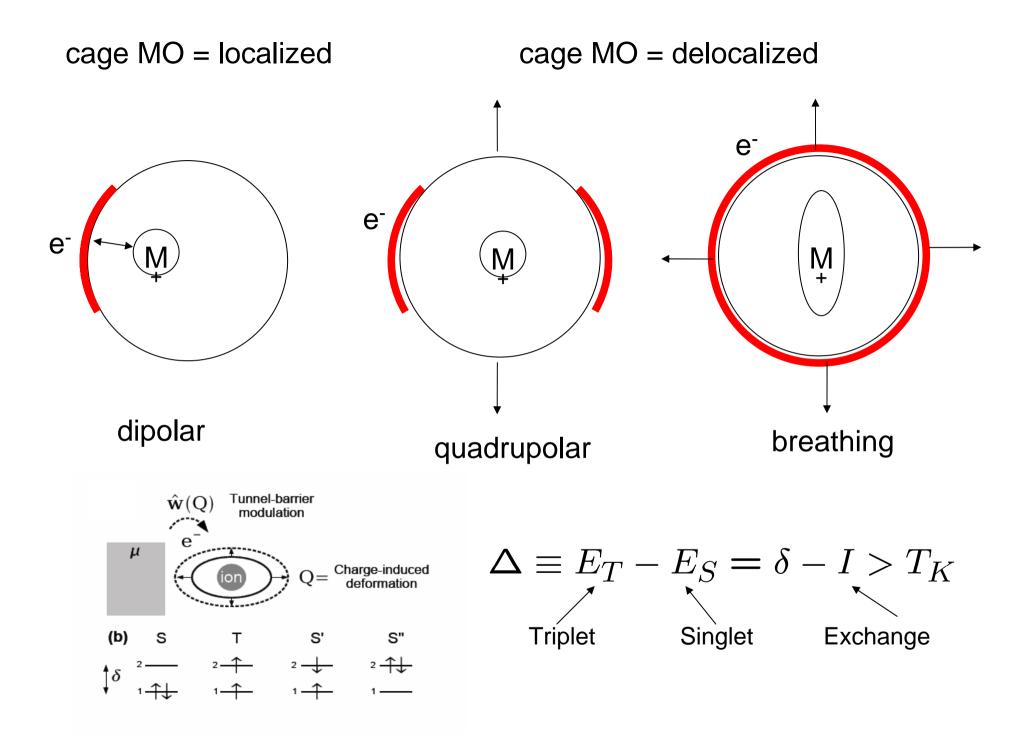
- Q: Can phonons assist a resonance tunneling?
- A: Yes, they can do it through dynamical symmetries.

Phonons + Kondo = "Phondo"

Effective model



$$H_{res} + H_{tun} = \sum_{k\sigma} \epsilon_k c^{\dagger}_{k\sigma} c_{k\sigma} + \hat{w}_Q \sum_{k\mu\sigma} \left(\tilde{d}^{\dagger}_{\mu\sigma} c_{k\sigma} + H.c. \right)$$

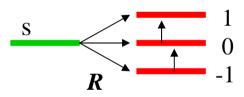


TMOC = Transition Metal + Organic Complex (cage)





Singlet Triplet



Assumption: even electron occupation number

Singlet is a ground state

SO(4) symmetry

$$H_{tun} = \hat{w}(Q) \sum_{k} \sum_{\Lambda \gamma \sigma}' [|\Lambda\rangle \langle \gamma | c_{k\sigma} + H.c.]$$

$$\frac{1}{\Lambda S^2} = \hat{I}_{\sigma} S + \hat{I}_{\sigma} S + \hat{I}_{\sigma} B + \hat{I}_{\sigma} B + \hat{I}_{\sigma} D^2$$

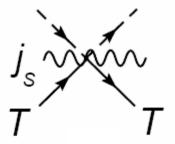
$$H_{eff} = H_{res} + \frac{1}{2}\Delta \mathbf{S}^2 + \hat{J}_S \mathbf{S} \cdot \mathbf{s} + \hat{J}_R \mathbf{R} \cdot \mathbf{s} + \frac{M}{2}P^2$$

Local phonon can be emitted or absorbed in a co-tunneling processes The main source of phonon emission/absorption is the tunneling rate Vibration assisted tunneling

$$H_{eff} = H_{res} + \frac{1}{2}\Delta \mathbf{S}^2 + \hat{J}_S \mathbf{S} \cdot \mathbf{s} + \hat{J}_R \mathbf{R} \cdot \mathbf{s} + \frac{\Omega}{2}P^2$$

 $\widehat{J}_S(Q) = J_S + j_S Q^2, \qquad \widehat{J}_R(Q) = J_R + j_R Q$



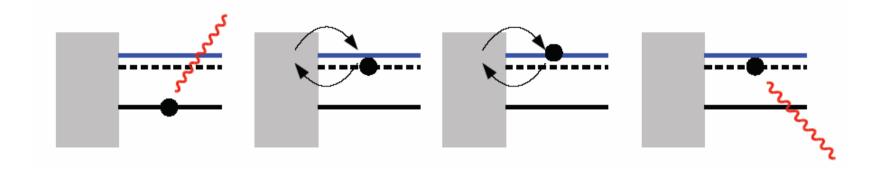


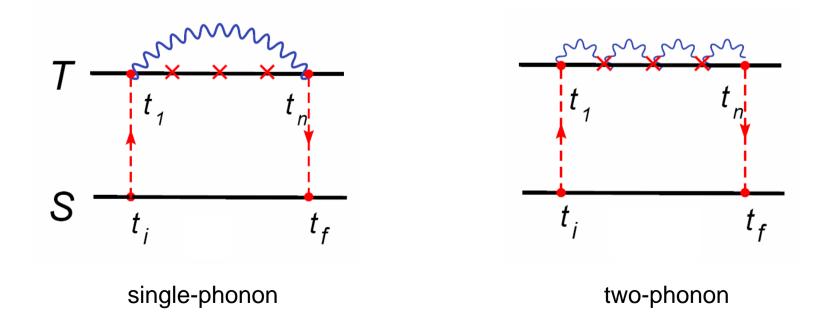
single phonon

two-phonon

 $j_S \ll j_R$

Phonon assisted processes

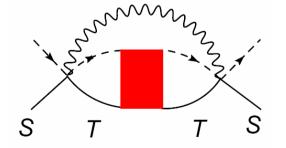




Single phonon processes

$$\gamma^{(1)} \sim j_R^2 \int \frac{d\epsilon}{2\pi} \int \frac{d\omega}{2\pi} \tanh\left(\frac{\epsilon}{2T}\right) Im \mathcal{G}^R(\epsilon) Re \bar{G}^R(\omega) Im D^R(\epsilon - \omega) \coth\left(\frac{\epsilon - \omega}{2T}\right)$$
$$\gamma^{(1)} = \gamma^{(2)} \sim \rho j_R^2 \log\left(\frac{D}{max[T, |\Delta - \Omega_0|]}\right)$$

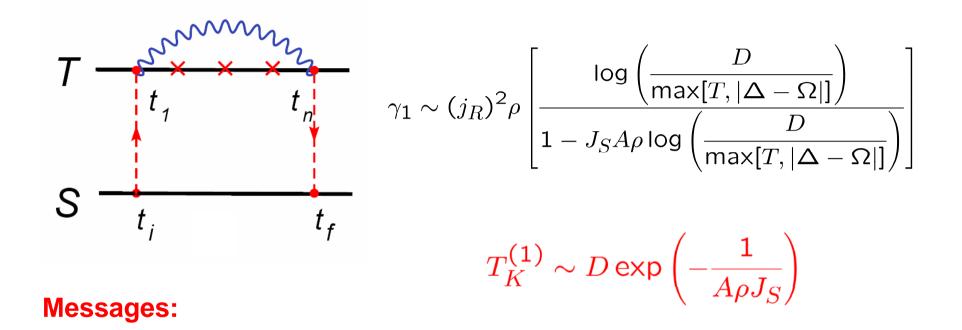
$$\gamma^{(2)} \sim j_R^2 \int \frac{d\epsilon}{2\pi} \int \frac{d\omega}{2\pi} \tanh\left(\frac{\epsilon}{2T}\right) Im \mathcal{G}^R(\epsilon) Re \bar{G}^R(\omega) Im D^R(-\epsilon - \omega) \coth\left(\frac{\epsilon + \omega}{2T}\right)$$



Summation of "parquet" diagrams

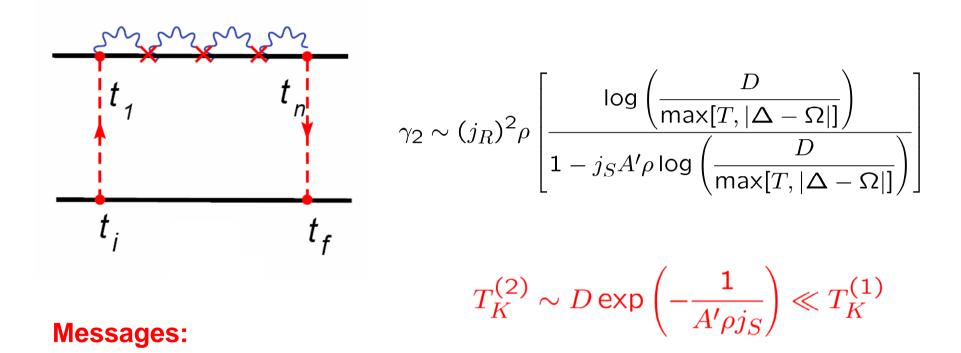
$$\gamma_1 \sim j_R^2 \int \frac{d\epsilon}{2\pi} \coth\left(\frac{\epsilon}{2T}\right) \left[Re\left[\frac{\Pi(-\epsilon)}{1 - J_0^T \bar{\Pi}(-\epsilon)}\right]^R Im D^R(\epsilon) + ReD^R(-\epsilon) Im\left[\frac{\Pi_i(\epsilon)}{1 - J_0^T \bar{\Pi}(\epsilon)}\right]^R \right]$$

Single phonon processes



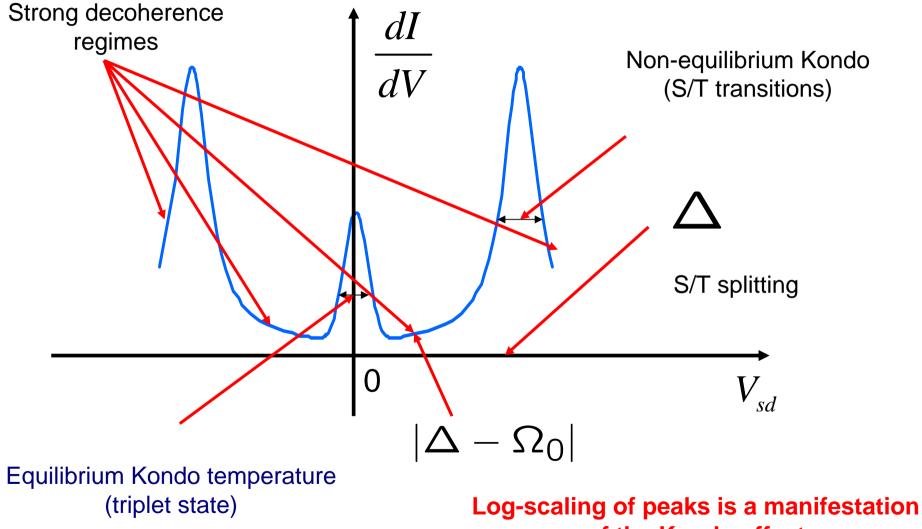
- Single phonon processes assist the Kondo tunneling
- Kondo temperature does not depend on the phonon coupling
- Differential conductance is logarithmically enhanced approaching the Kondo regime

Two-phonon processes



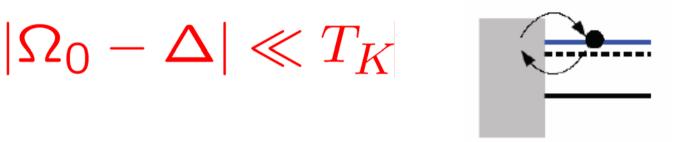
- Two-phonon processes also assist the Kondo tunneling, however
- Kondo temperature **depends** on the phonon coupling
- The two phonon scenario leads to much smaller Kondo temperatures

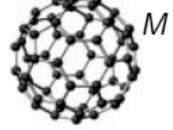
Differential Conductance



of the Kondo effect

A resonance condition



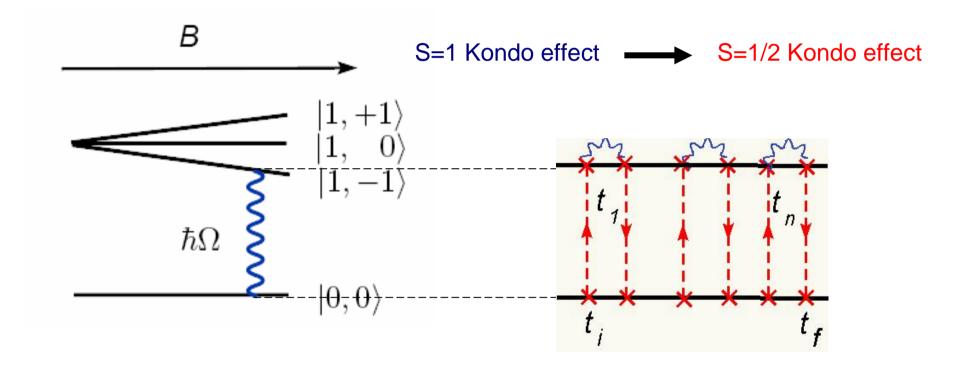


... narrows a group of the TMOC with "Phondo".

What happens if $T_K < |\Omega_0 - \Delta| \ll \Delta$?

Fine tuning tool is necessary to control the resonance

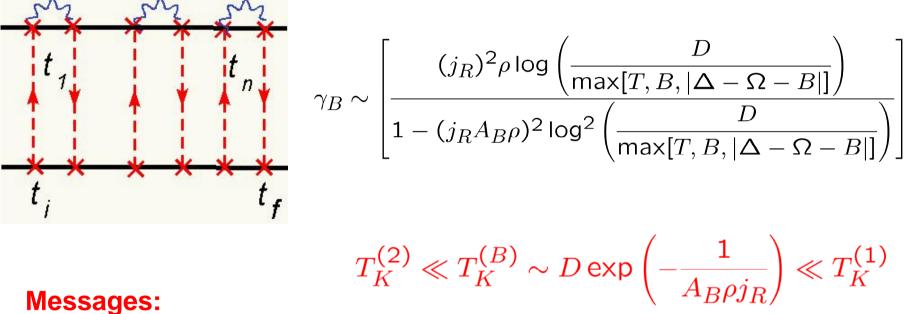
Magnetic Field Effects



Magnetic field as a fine tuning tool

M.Pustilnik, Y.Avishai, K.Kikoin, PRL 2000

Single-phonon processes in magnetic field

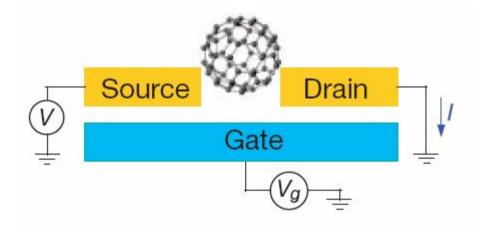


- messayes.
- Single-phonon processes assist the Kondo tunneling, however
- Kondo temperature depends on the phonon coupling
- Magnetic field provides a tool for the fine tuning of the TMOC

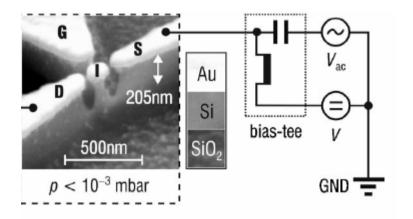
NEM-SET with center-of-mass motion = Mobile Kondo Impurity

Molecular Transistor

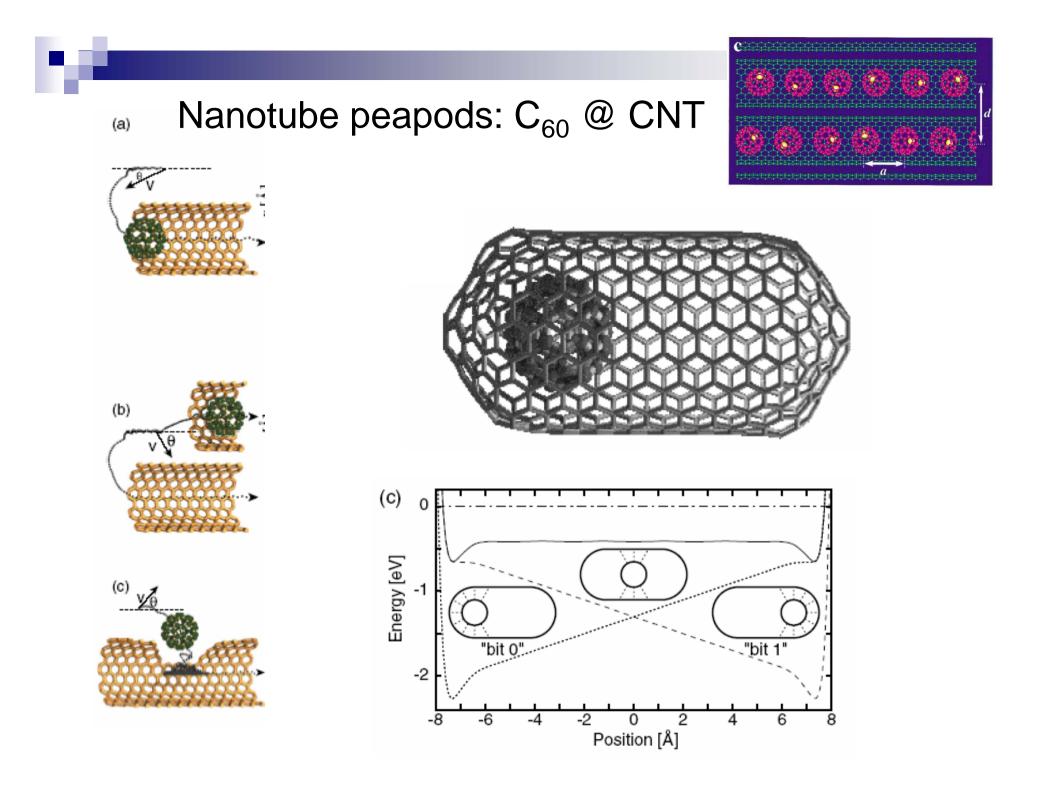
Nano-Pendulum

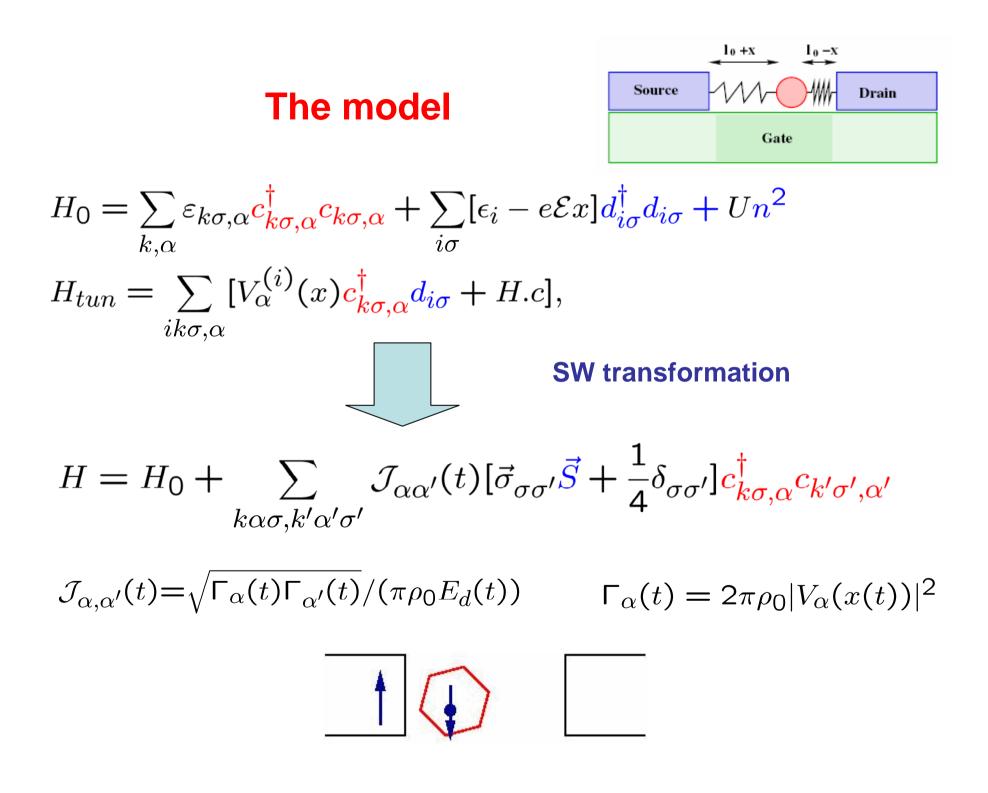


H.Park et al, Nature 2000

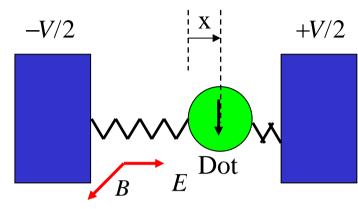


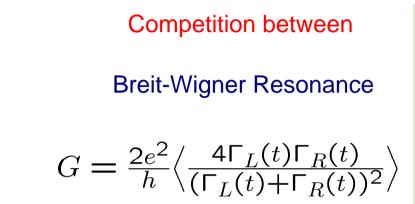
D.Sheible and R.Blick 2004

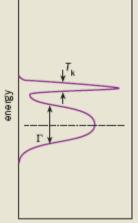




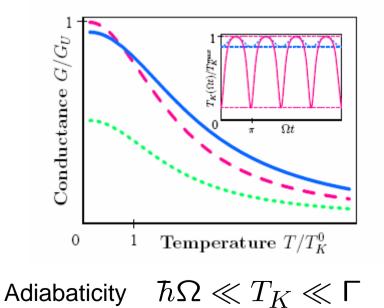
Odd-spin Kondo shuttle







Abrikosov-Suhl Resonance

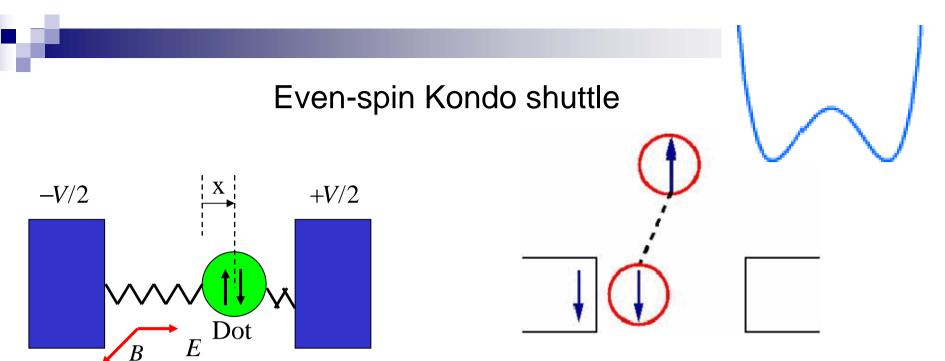


$$G(T) = \frac{3\pi^2}{16} G_U \left\langle \frac{4\Gamma_L(t)\Gamma_R(t)}{(\Gamma_L(t) + \Gamma_R(t))^2} \frac{1}{[\ln(T/T_K(t))]^2} \right\rangle$$

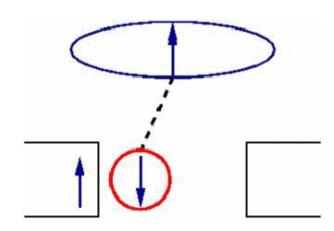
$$T_K(t) = D(t) \exp\left[-\frac{\pi U}{8\Gamma_0 \cosh(2x(t)/\lambda_0)}\right]$$

$$\langle T_K \rangle = T_K^0 \langle \exp\left[\frac{\pi U}{4\Gamma_0} \frac{\sinh^2(x(t)/\lambda_0)}{1+2\sinh^2(x(t)/\lambda_0)}\right] \rangle$$

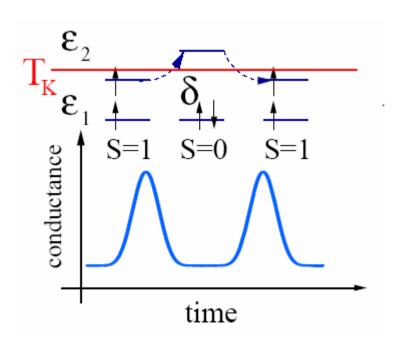
Time-dependent Kondo temperatures



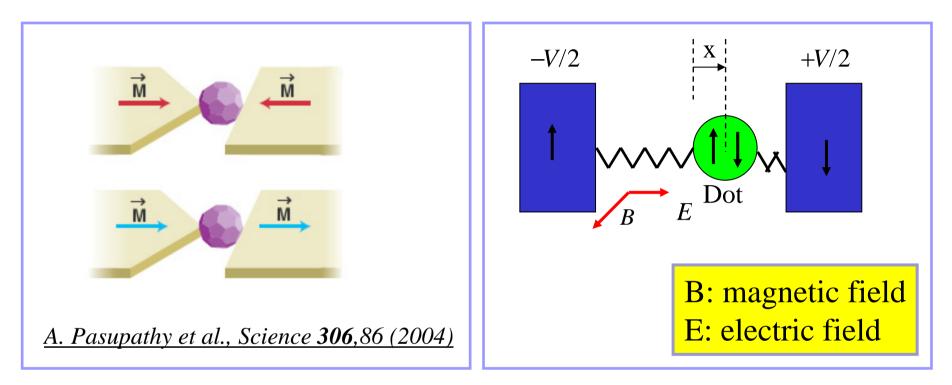
Singlet shuttling: No Kondo effect



Triplet Kondo Shuttling



Perspectives



- NEM-SET between spin-polarized leads
- NEM spin manipulation
- Rotating pendulum
- Coupled NEM-SET devices (DQD, TQD)

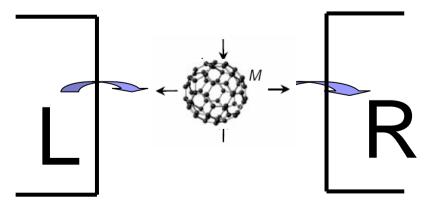


Conclusions

Molecular Transistor

M

- Phonon emission/absorption induces the Kondo tunneling
- Dynamical symmetries allow Kondo effect in excited triplet state
- Decoherence due to vibration does not destroy the Kondo effect





Conclusions

Molecular Transistor

M

- Phonon emission/absorption induces the Kondo tunneling
- Dynamical symmetries allow Kondo effect in excited triplet state
- Decoherence due to vibration does not destroy the Kondo effect

Kondo shuttle

- Kondo shuttling allows the spin manipulation by NEM motion
- Kondo NEM-SET is a Mobile Quantum Impurity
- Dynamical symmetries influence the Kondo shuttling in S/T setups